

UNITED STATES PATENT AND TRADEMARK OFFICE



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.usplo.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	 ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/497,508	02/04/2000	Jin Jang	 8733.20079	7572
30827 7	590 06/01/2004		EXAMINER	
MCKENNA LONG & ALDRIDGE LLP 1900 K STREET, NW		LLP	LOUIE, WAI SING	
	N, DC 20006		ART UNIT	PAPER NUMBER
		v.	 2814	
			DATE MAILED: 06/01/2004	1

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)		
Office Action Summary	09/497,508	JANG ET AL.		
Office Action Summary	Examiner	Art Unit	2	
	Wai-Sing Louie	2814	12	
The MAILING DATE of this communication a Period for Reply	ppears on the cover sheet wil	n tne correspondence addr	'ess	
A SHORTENED STATUTORY PERIOD FOR REP THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory perio - Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).	I. 1.136(a). In no event, however, may a re the ply within the statutory minimum of thirty d will apply and will expire SIX (6) MON tte, cause the application to become AB.	ply be timely filed r (30) days will be considered timely. I'HS from the mailing date of this comi ANDONED (35 U.S.C. § 133).	munication.	
Status				
1) Responsive to communication(s) filed on 09	April 2004.			
	nis action is non-final.			
3) Since this application is in condition for allow	ance except for formal matte	ers, prosecution as to the n	nerits is	
closed in accordance with the practice under	Ex parte Quayle, 1935 C.D.	11, 453 O.G. 213.		
Disposition of Claims				
	lication	•		
4) Claim(s) <u>1-7 and 9</u> is/are pending in the appl 4a) Of the above claim(s) is/are withdr	,			
5) Claim(s) is/are allowed.	awii iioiii congideration.			
6)⊠ Claim(s) <u>1-7 and 9</u> is/are rejected.	•			
7) Claim(s) is/are objected to.				
8) Claim(s) are subject to restriction and	/or election requirement.			
Augliostica Bonon				
Application Papers				
9) The specification is objected to by the Examin				
10) The drawing(s) filed on is/are: a) a				
Applicant may not request that any objection to the Replacement drawing sheet(s) including the corre			₹ 1 121(d)	
11) The oath or declaration is objected to by the	·			
			и	
Priority under 35 U.S.C. § 119		•		
12)⊠ Acknowledgment is made of a claim for foreional a)⊠ All b)□ Some * c)□ None of:	gn priority under 35 U.S.C. §	119(a)-(d) or (f).		
 Certified copies of the priority docume 				
2. Certified copies of the priority docume				
3. Copies of the certified copies of the pr		received in this National S	tage	
application from the International Bure * See the attached detailed Office action for a li		ropoiyad	•	
See the attached detailed Office action for a in	st of the certified copies not	received.		
	·			
Attachment(s)				
1) Notice of References Cited (PTO-892)	4) 🔲 Interview S	ummary (PTO-413)		
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date	150)	
 Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date 	(8) 5) ☐ Notice of Ir 6) ☐ Other:	formal Patent Application (PTO-1 	192)	
C. Dutant and Tendemody Office	-,			

Application/Control Number: 09/497,508

Art Unit: 2814

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-7 and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Miyanaga et al. (US 5,932,983), newly cited, in view of Fonash et al. (US 5,994,164), previously applied.

With regard to claims 1, 3, 6, and 9, Miyanaga et al. disclose a semiconductor device having doped polycrystalline layer (col. 11, line 8 to col. 21, line 45) comprising:

- Containing metal atoms, nickel, having a density range of $1x10^{17}$ to $1x10^{20}$ atoms/cm³ on average, where the metal is a catalyst for metal induced crystallization of amorphous silicon (col. 8, lines 41-60 and fig. 4);
- The polycrystalline silicon film is formed on an insulating substrate (col. 18, lines 40-44);
- The polycrystalline silicon film comprises a plurality of the crystallites is needlelike (Miyanaga col. 7, lines 31-35);
- Miyanaga et al. do not disclose an electrical conductivity activation energy
 between 0.52 to 0.71 eV. However, Fonash et al. disclose forming a
 polycrystalline film with nickel as a catalyst element similar to Miyanaga (Fonash

Application/Control Number: 09/497,508

Art Unit: 2814

col. 3, lines 38-49), where the conductivity activation energy is 0.52 eV @ 290°C (Fonash fig. 8b). Therefore, it would have been obvious in light of the teaching of Fonash et al. that the claimed activation energy is achieved when polycrystalline film has nickel as catalyst. Since the applicant has not established the criticality of the activation energy stated and since these values are in common use in similar devices in the art, it would have been obvious to one of ordinary skill in the art to use these values in the device. Where patentability is said to be based upon particular chosen dimension or upon another variable recited in a claim, the applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

With regard to claims 2, 5, and 7, Miyanaga et al. disclose the polycrystalline silicon film is formed by crystallizing an amorphous silicon film containing Ni atoms (see discussion with respect to claim 1 above) by means of thermal treatment with a lamp annealing process and the lamp produces a electric field which applies the electric field onto the silicon film (col. 12, line 43-59).

With regard to claim 4, Miyanaga et al. disclose an oxide layer 102 (col. 11, line 35) is in between the insulating substrate 101 and amorphous silicon film 104, which crystallizes into polycrystalline silicon film (col. 12, lines 43-59 and fig. 1b).

Response to Arguments

Application/Control Number: 09/497,508

Art Unit: 2814

Page 4

Applicant's arguments with respect to claims 1-9 have been considered but are most in view of the new ground(s) of rejection with the newly cited reference, Miyanaga et al. (US 5,932,983).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wai-Sing Louie whose telephone number is (571) 272-1709. The examiner can normally be reached on 7:30 AM to 4:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Wsl

May 28, 2004.

Wael Falonny SPE 2814